SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

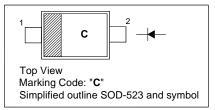
for low current rectification and high speed switching applications

Features

• Extremely small surface mounting type

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	30	V
Mean Rectifying Current	Io	200	mA
Peak Forward Surge Current (60Hz for Cyc.)	I _{FSM}	1	А
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _s	- 40 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 200 mA	V _F	0.5	V
Reverse Current at V _R = 10 V	I _R	30	μΑ





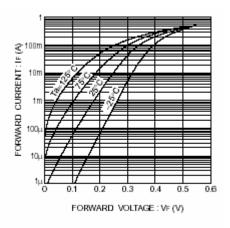


Fig. 1 Forward characteristics

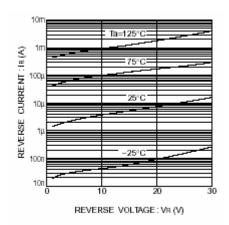


Fig. 2 Reverse characteristics

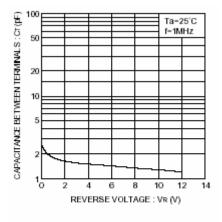


Fig. 3 Capacitance between terminals characteristics

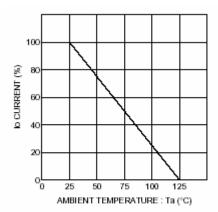


Fig. 4 Derating curve (mounting on glass epoxy PCBs)





(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)







PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523

